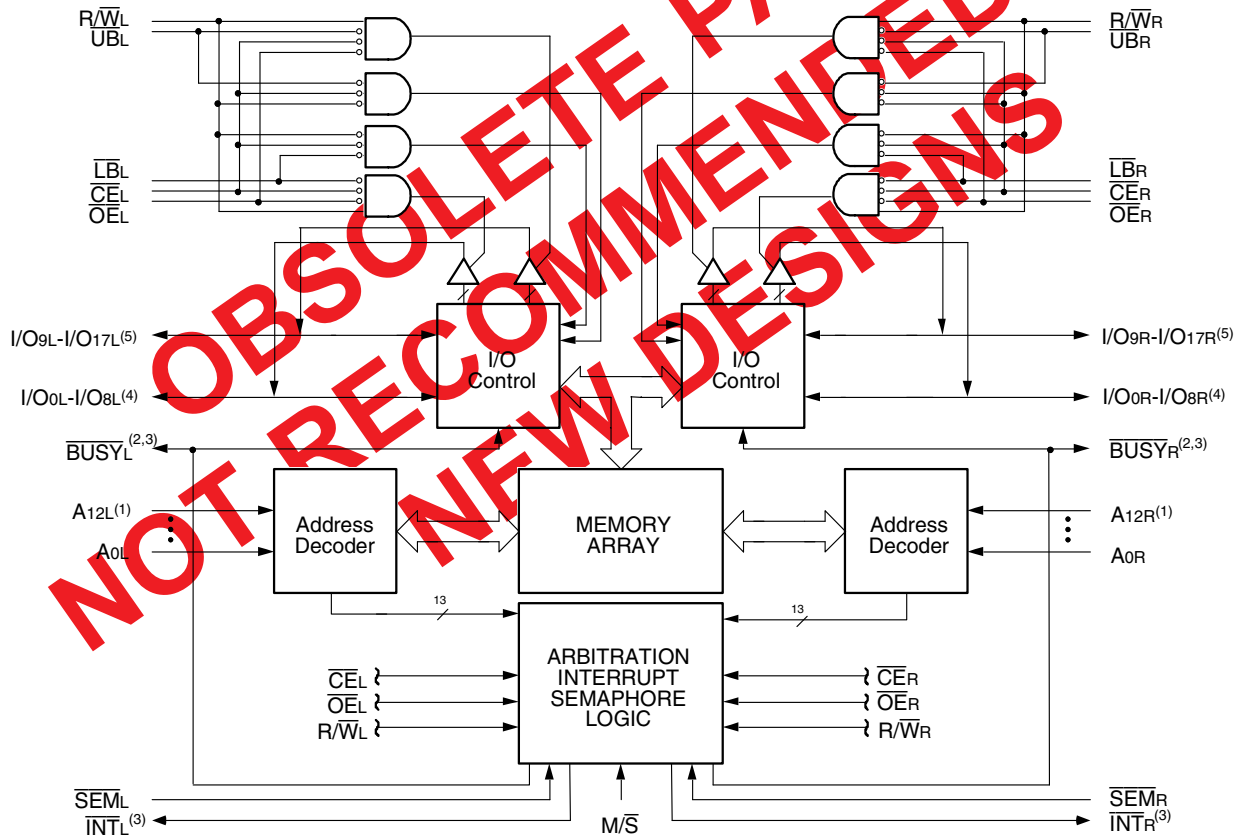


**Features**

- ◆ True Dual-Ported memory cells which allow simultaneous reads of the same memory location
- ◆ High-speed access  
IDT70T35/34L (IDT70T25/24L)
  - Commercial: 20/25ns (max.)
  - Industrial: 25ns (max.)
- ◆ Low-power operation
  - IDT70T35/34L (IDT70T25/24L)
  - Active: 200mW (typ.)
  - Standby: 600μW (typ.)
- ◆ Separate upper-byte and lower-byte control for multiplexed bus compatibility
- ◆ IDT70T35/34L (IDT70T25/24L) easily expands data bus width to 36 bits (32 bits) or more using the Master/Slave
  - select when cascading more than one device
  - ◆  $M/\bar{S} = V_{IH}$  for  $\overline{BUSY}$  output flag on Master
  - ◆  $M/\bar{S} = V_{IL}$  for  $\overline{BUSY}$  input on Slave
  - ◆  $\overline{BUSY}$  and Interrupt Flag
  - ◆ On-chip port arbitration logic
  - ◆ Full on-chip hardware support of semaphore signaling between ports
  - ◆ Fully asynchronous operation from either port
  - ◆ LVTTTL-compatible, single 2.5V ( $\pm 100mV$ ) power supply
  - ◆ Available in a 100-pin Thin Quad Flatpack (TQFP) package and 100-pin fine pitch Ball Grid Array (fpBGA)
  - ◆ Industrial temperature range (-40°C to +85°C) is available for selected speeds

**Functional Block Diagram**



**NOTES:**

1. A12 is a NC for IDT70T34 and IDT70T24.
2. (MASTER):  $\overline{BUSY}$  is output; (SLAVE):  $\overline{BUSY}$  is input.
3.  $\overline{BUSY}$  outputs and  $\overline{INT}$  outputs are non-tri-stated push-pull.
4. I/O0x - I/O7x for IDT70T25/24.
5. I/O8x - I/O15x for IDT70T25/24.

5639 drw 01

## Description

The IDT70T35/34L (IDT70T25/24L) is a high-speed 8/4K x 18 (8/4K x 16) Dual-Port Static RAM. The IDT70T35/34L (IDT70T25/24L) is designed to be used as a stand-alone Dual-Port RAM or as a combination MASTER/SLAVE Dual-Port RAM for 36-bit (32-bit) or wider memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

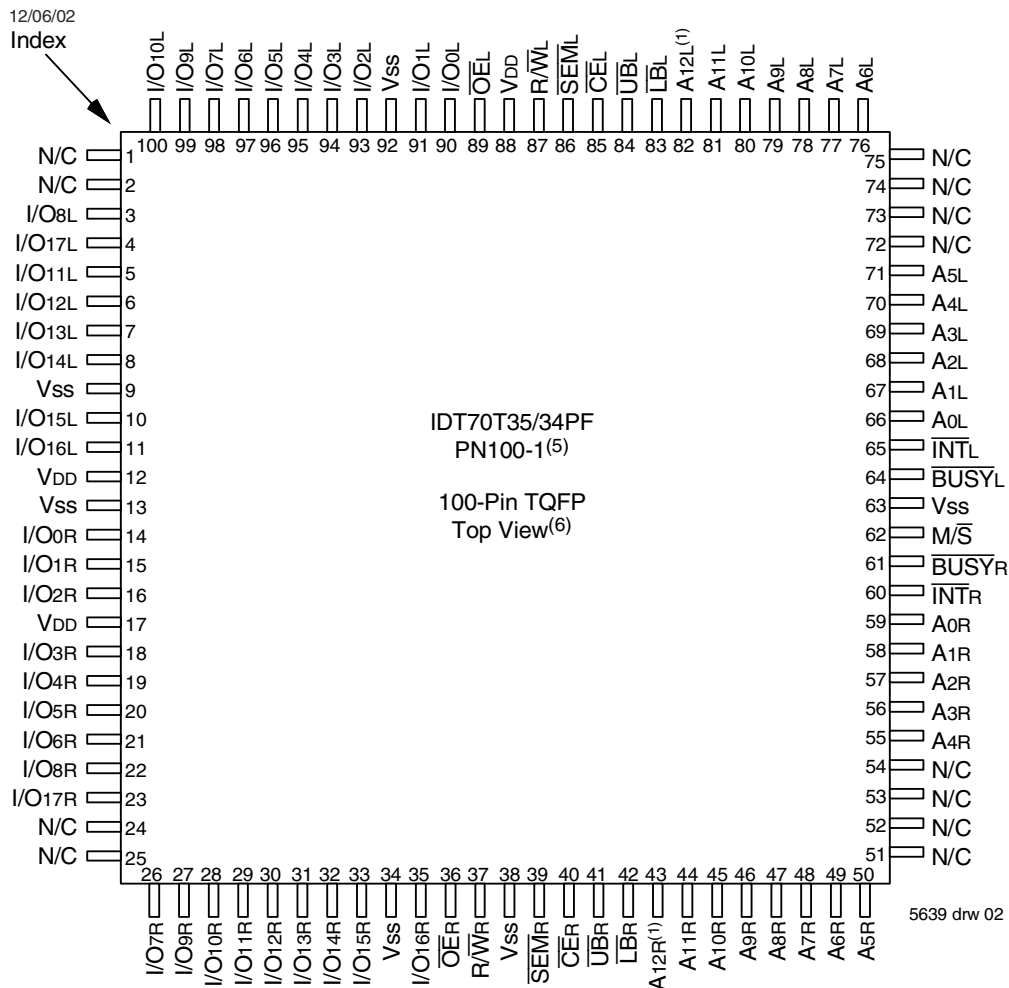
This device provides two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for

reads or writes to any location in memory. An automatic power down feature controlled by  $\overline{CE}$  permits the on-chip circuitry of each port to enter a very low standby power mode.

Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 200mW of power.

The IDT70T35/34L (IDT70T25/24L) is packaged in a plastic 100-pin Thin Quad Flatpack and a 100-pin fine pitch Ball Grid Array.

## IDT70T35/34 Pin Configurations<sup>(1,2,3,4)</sup>



### NOTES:

1. A12 is a NC for IDT70T34.
2. All VDD pins must be connected to power supply.
3. All Vss pins must be connected to ground.
4. PN100-1 package body is approximately 14mm x 14mm x 1.4mm.
5. This package code is used to reference the package diagram.
6. This text does not indicate orientation of the actual part marking.

## IDT70T35/34 Pin Configurations(cont'd) (1,2,3,4)

IDT70T35/34BF  
BF100<sup>(5)</sup>

100-Pin fpBGA  
Top View<sup>(6)</sup>

12/06/02

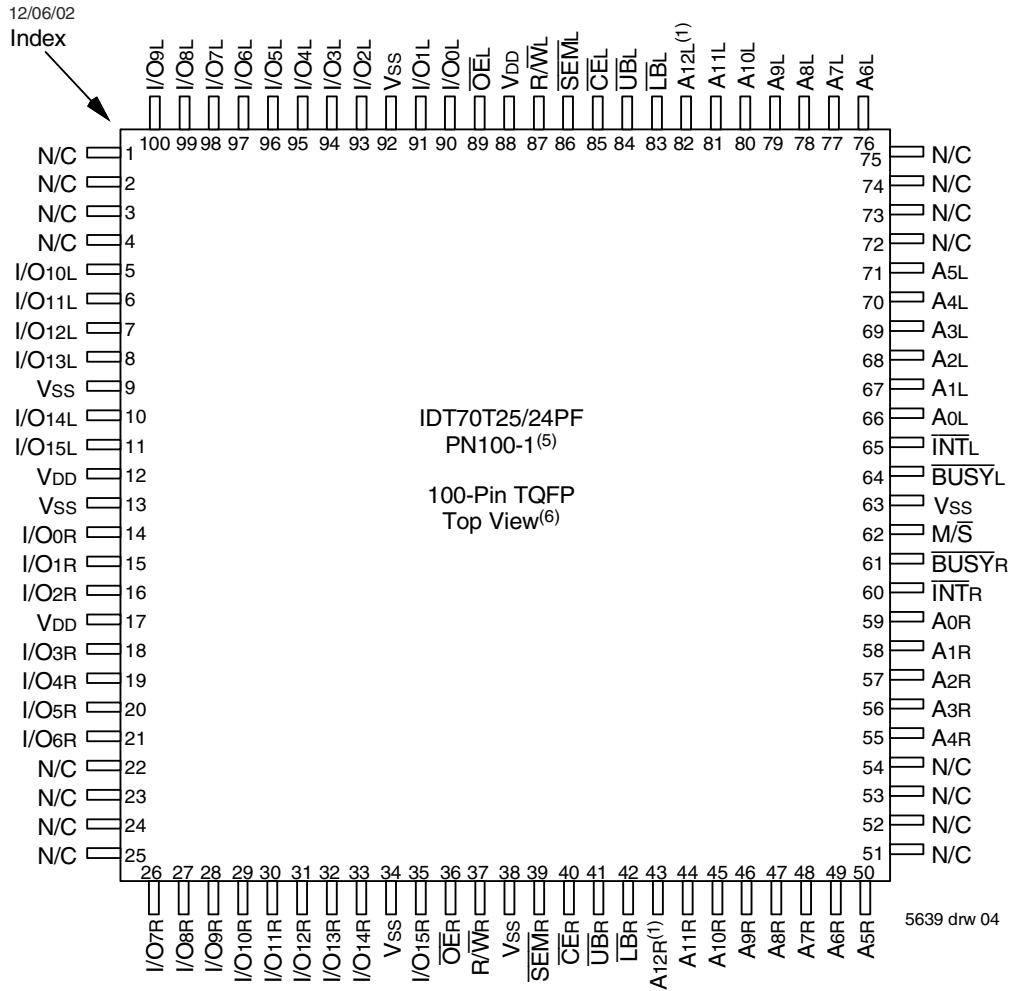
A1 A6R	A2 A9R	A3 A12R <sup>(1)</sup>	A4 $\overline{\text{CE}}\text{R}$	A5 VSS	A6 VSS	A7 VSS	A8 I/O13R	A9 I/O10R	A10 I/O7R
B1 NC	B2 NC	B3 A8R	B4 A10R	B5 $\overline{\text{SEM}}\text{R}$	B6 R/W $\overline{\text{R}}$	B7 $\overline{\text{OE}}\text{R}$	B8 I/O12R	B9 I/O9R	B10 I/O6R
C1 A3R	C2 A4R	C3 A5R	C4 A7R	C5 $\overline{\text{UB}}\text{R}$	C6 I/O16R	C7 I/O15R	C8 I/O11R	C9 I/O8R	C10 I/O3R
D1 A1R	D2 $\overline{\text{INT}}\text{R}$	D3 A2R	D4 NC	D5 A11R	D6 $\overline{\text{LB}}\text{R}$	D7 I/O14R	D8 I/O17R	D9 I/O5R	D10 I/O1R
E1 M/S $\overline{\text{S}}$	E2 $\overline{\text{BUSY}}\text{R}$	E3 A0R	E4 A1L	E5 VSS	E6 VSS	E7 I/O4R	E8 I/O2R	E9 I/O0R	E10 VDD
F1 VSS	F2 $\overline{\text{BUSY}}\text{L}$	F3 A0L	F4 NC	F5 VDD	F6 VSS	F7 VDD	F8 I/O14L	F9 I/O15L	F10 I/O16L
G1 $\overline{\text{INT}}\text{L}$	G2 A3L	G3 A6L	G4 NC	G5 VSS	G6 I/O3L	G7 NC	G8 I/O12L	G9 VSS	G10 I/O13L
H1 A2L	H2 A5L	H3 A10L	H4 $\overline{\text{LB}}\text{L}$	H5 $\overline{\text{CE}}\text{L}$	H6 I/O1L	H7 I/O7L	H8 I/O8L	H9 I/O17L	H10 I/O11L
J1 A4L	J2 A8L	J3 A11L	J4 $\overline{\text{SEM}}\text{L}$	J5 R/W $\overline{\text{L}}$	J6 $\overline{\text{OE}}\text{L}$	J7 I/O4L	J8 I/O6L	J9 VSS	J10 I/O10L
K1 A7L	K2 A9L	K3 A12L <sup>(1)</sup>	K4 $\overline{\text{UB}}\text{L}$	K5 VDD	K6 VDD	K7 I/O0L	K8 I/O2L	K9 I/O5L	K10 I/O9L

5639 drw 03

### NOTES:

1. A12 is a NC for IDT70T34.
2. All VDD pins must be connected to power supply.
3. All VSS pins must be connected to ground.
4. BF-100 package body is approximately 10mm x 10mm x 1.4mm with 0.8mm ball pitch.
5. This package code is used to reference the package diagram.
6. This text does not indicate orientation of the actual part marking.

## IDT70T25/24 Pin Configurations<sup>(1,2,3,4)</sup>



**NOTES:**

1. A12 is a NC for IDT70T24.
2. All VDD pins must be connected to power supply.
3. All VSS pins must be connected to ground.
4. PN100-1 package body is approximately 14mm x 14mm x 1.4mm.
5. This package code is used to reference the package diagram.
6. This text does not indicate orientation of the actual part marking.

## IDT70T25/24 Pin Configurations(cont'd) (1,2,3,4)

IDT70T25/24BF  
BF100<sup>(5)</sup>

100-Pin fpBGA  
Top View<sup>(6)</sup>

12/06/02

A1 A6R	A2 A9R	A3 A12R <sup>(1)</sup>	A4 $\overline{\text{CE}}\text{R}$	A5 VSS	A6 VSS	A7 VSS	A8 I/O12R	A9 I/O9R	A10 I/O7R
B1 NC	B2 NC	B3 A8R	B4 A10R	B5 $\overline{\text{SE}}\text{MR}$	B6 R/ $\overline{\text{W}}\text{R}$	B7 $\overline{\text{OE}}\text{R}$	B8 I/O11R	B9 I/O8R	B10 I/O6R
C1 A3R	C2 A4R	C3 A5R	C4 A7R	C5 $\overline{\text{UB}}\text{R}$	C6 I/O15R	C7 I/O14R	C8 I/O10R	C9 NC	C10 I/O3R
D1 A1R	D2 $\overline{\text{INT}}\text{R}$	D3 A2R	D4 NC	D5 A11R	D6 $\overline{\text{LB}}\text{R}$	D7 I/O13R	D8 NC	D9 I/O5R	D10 I/O1R
E1 M/ $\overline{\text{S}}$	E2 $\overline{\text{BUSY}}\text{R}$	E3 A0R	E4 A1L	E5 VSS	E6 VSS	E7 I/O4R	E8 I/O2R	E9 I/O0R	E10 VDD
F1 VSS	F2 $\overline{\text{BUSY}}\text{L}$	F3 A0L	F4 NC	F5 VDD	F6 VSS	F7 VDD	F8 I/O13L	F9 I/O14L	F10 I/O15L
G1 $\overline{\text{INT}}\text{L}$	G2 A3L	G3 A6L	G4 NC	G5 VSS	G6 I/O3L	G7 NC	G8 I/O11L	G9 VSS	G10 I/O12L
H1 A2L	H2 A5L	H3 A10L	H4 $\overline{\text{LB}}\text{L}$	H5 $\overline{\text{CE}}\text{L}$	H6 I/O1L	H7 I/O7L	H8 NC	H9 NC	H10 I/O10L
J1 A4L	J2 A8L	J3 A11L	J4 $\overline{\text{SE}}\text{ML}$	J5 R/ $\overline{\text{W}}\text{L}$	J6 $\overline{\text{OE}}\text{L}$	J7 I/O4L	J8 I/O6L	J9 VSS	J10 I/O9L
K1 A7L	K2 A9L	K3 A12L <sup>(1)</sup>	K4 $\overline{\text{UB}}\text{L}$	K5 VDD	K6 VDD	K7 I/O0L	K8 I/O2L	K9 I/O5L	K10 I/O8L

5639 drw 05

### NOTES:

1. A12 is a NC for IDT70T24.
2. All VDD pins must be connected to power supply.
3. All VSS pins must be connected to ground.
4. BF-100 package body is approximately 10mm x 10mm x 1.4mm with 0.8mm ball pitch.
5. This package code is used to reference the package diagram.
6. This text does not indicate orientation of the actual part marking.

## Pin Names

Left Port	Right Port	Names
$\overline{CE}_L$	$\overline{CE}_R$	Chip Enable
$R/\overline{WL}$	$R/\overline{WR}$	Read/Write Enable
$\overline{OE}_L$	$\overline{OE}_R$	Output Enable
A <sub>0L</sub> - A <sub>12L</sub> <sup>(1)</sup>	A <sub>0R</sub> - A <sub>12R</sub> <sup>(1)</sup>	Address
I/O <sub>0L</sub> - I/O <sub>17L</sub> <sup>(2)</sup>	I/O <sub>0R</sub> - I/O <sub>17R</sub> <sup>(2)</sup>	Data Input/Output
$\overline{SEM}_L$	$\overline{SEM}_R$	Semaphore Enable
$\overline{UB}_L$	$\overline{UB}_R$	Upper Byte Select <sup>(3)</sup>
$\overline{LB}_L$	$\overline{LB}_R$	Lower Byte Select <sup>(4)</sup>
$\overline{INT}_L$	$\overline{INT}_R$	Interrupt Flag
$\overline{BUSY}_L$	$\overline{BUSY}_R$	Busy Flag
M/ $\overline{S}$		Master or Slave Select
V <sub>DD</sub>		Power (2.5V)
V <sub>SS</sub>		Ground (0V)

5639 tbl 01

### NOTE:

1. A<sub>12</sub> is a NC for IDT70T34 and IDT70T24.
2. I/O<sub>0x</sub> - I/O<sub>15x</sub> for IDT70T25/24.
3. IDT70T35/34L:  $\overline{UB}_x$  controls I/O<sub>9x</sub> - I/O<sub>17x</sub>  
IDT70T25/24L:  $\overline{UB}_x$  controls I/O<sub>8x</sub> - I/O<sub>15x</sub>
4. IDT70T35/34L:  $\overline{LB}_x$  controls I/O<sub>0x</sub> - I/O<sub>8x</sub>  
IDT70T25/24L:  $\overline{LB}_x$  controls I/O<sub>0x</sub> - I/O<sub>7x</sub>

### Truth Table I: Non-Contention Read/Write Control

Inputs <sup>(1)</sup>						Outputs		Mode
$\overline{CE}$	R/ $\overline{W}$	$\overline{OE}$	$\overline{UB}$	$\overline{LB}$	$\overline{SEM}$	I/O <sub>9-17</sub> <sup>(3)</sup>	I/O <sub>0-8</sub> <sup>(2)</sup>	
H	X	X	X	X	H	High-Z	High-Z	Deselected: Power Down
X	X	X	H	H	H	High-Z	High-Z	Both Bytes Deselected
L	L	X	L	H	H	DATA <sub>IN</sub>	High-Z	Write to Upper Byte Only
L	L	X	H	L	H	High-Z	DATA <sub>IN</sub>	Write to Lower Byte Only
L	L	X	L	L	H	DATA <sub>IN</sub>	DATA <sub>IN</sub>	Write to Both Bytes
L	H	L	L	H	H	DATA <sub>OUT</sub>	High-Z	Read Upper Byte Only
L	H	L	H	L	H	High-Z	DATA <sub>OUT</sub>	Read Lower Byte Only
L	H	L	L	L	H	DATA <sub>OUT</sub>	DATA <sub>OUT</sub>	Read Both Bytes
X	X	H	X	X	X	High-Z	High-Z	Outputs Disabled

**NOTE:**

1. A<sub>0L</sub> — A<sub>12L</sub> ≠ A<sub>0R</sub> — A<sub>12R</sub> for IDT70T35 and IDT70T25; A<sub>0L</sub> — A<sub>11L</sub> ≠ A<sub>0R</sub> — A<sub>11R</sub> for IDT70T34 and IDT70T24.
2. Outputs for IDT70T25/24 are I/O<sub>0x</sub> - I/O<sub>7x</sub>.
3. Outputs for IDT70T25/24 are I/O<sub>8x</sub> - I/O<sub>15x</sub>.

5639 tbl 02

### Truth Table II: Semaphore Read/Write Control<sup>(1)</sup>

Inputs						Outputs		Mode
$\overline{CE}$	R/ $\overline{W}$	$\overline{OE}$	$\overline{UB}$	$\overline{LB}$	$\overline{SEM}$	I/O <sub>9-17</sub> <sup>(1)</sup>	I/O <sub>0-8</sub> <sup>(1)</sup>	
H	H	L	X	X	L	DATA <sub>OUT</sub>	DATA <sub>OUT</sub>	Read Data in Semaphore Flag
X	H	L	H	H	L	DATA <sub>OUT</sub>	DATA <sub>OUT</sub>	Read Data in Semaphore Flag
H	↑	X	X	X	L	DATA <sub>IN</sub>	DATA <sub>IN</sub>	Write D <sub>IN0</sub> into Semaphore Flag
X	↑	X	H	H	L	DATA <sub>IN</sub>	DATA <sub>IN</sub>	Write D <sub>IN0</sub> into Semaphore Flag
L	X	X	L	X	L	—	—	Not Allowed
L	X	X	X	L	L	—	—	Not Allowed

**NOTE:**

1. There are eight semaphore flags written to via I/O<sub>0</sub> and read from all of the I/O's (I/O<sub>0</sub>-I/O<sub>17</sub> for IDT70T35/34) and (I/O<sub>0</sub>-I/O<sub>15</sub> for IDT70T25/24). These eight semaphores are addressed by A<sub>0</sub>-A<sub>2</sub>.

5639 tbl 03

## Absolute Maximum Ratings<sup>(1)</sup>

Symbol	Rating	Commercial & Industrial	Unit
V <sub>TERM</sub> <sup>(2)</sup>	Terminal Voltage with Respect to GND	-0.5 to +3.6	V
T <sub>BIAS</sub> <sup>(3)</sup>	Temperature Under Bias	-55 to +125	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C
T <sub>JN</sub>	Junction Temperature	+150	°C
I <sub>OUT</sub>	DC Output Current	50	mA

5639 tbl 04

### NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- V<sub>TERM</sub> must not exceed V<sub>DD</sub> + 0.3V.
- Ambient Temperature Under DC Bias. No AC Conditions. Chip Deselected.

## Capacitance<sup>(1)</sup> (T<sub>A</sub> = +25°C, f = 1.0MHz)

Symbol	Parameter	Conditions <sup>(2)</sup>	Max.	Unit
C <sub>IN</sub>	Input Capacitance	V <sub>IN</sub> = 3dV	9	pF
C <sub>OUT</sub>	Output Capacitance	V <sub>OUT</sub> = 3dV	10	pF

5639 tbl 07

### NOTES:

- This parameter is determined by device characterization but is not production tested.
- 3dV references the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

## Maximum Operating Temperature and Supply Voltage<sup>(1)</sup>

Grade	Ambient Temperature	GND	V <sub>DD</sub>
Commercial	0°C to +70°C	0V	2.5V ± 100mV
Industrial	-40°C to +85°C	0V	2.5V ± 100mV

5639 tbl 05

### NOTE:

- This is the parameter T<sub>A</sub>. This is the "instant on" case temperature.

## Recommended DC Operating Conditions

Symbol	Parameter	Min.	Typ.	Max.	Unit
V <sub>DD</sub>	Supply Voltage	2.4	2.5	2.6	V
V <sub>SS</sub>	Ground	0	0	0	V
V <sub>IH</sub>	Input High Voltage	1.7	—	V <sub>DD</sub> +0.3 <sup>(2)</sup>	V
V <sub>IL</sub>	Input Low Voltage	-0.3 <sup>(1)</sup>	—	0.7	V

5639 tbl 06

### NOTES:

- V<sub>IL</sub> ≥ -1.5V for pulse width less than 10ns.
- V<sub>TERM</sub> must not exceed V<sub>DD</sub> + 0.3V.

## DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (V<sub>DD</sub> = 2.5V ± 100mV)

Symbol	Parameter	Test Conditions	70T35/34L (70T25/24L)		Unit
			Min.	Max.	
I <sub>LI</sub>	Input Leakage Current <sup>(1)</sup>	V <sub>DD</sub> = 2.6V, V <sub>IN</sub> = 0V to V <sub>DD</sub>	—	5	μA
I <sub>LO</sub>	Output Leakage Current <sup>(1)</sup>	$\overline{CE} = V_{IH}$ , V <sub>OUT</sub> = 0V to V <sub>DD</sub>	—	5	μA
V <sub>OL</sub>	Output Low Voltage	I <sub>OL</sub> = +2mA	—	0.4	V
V <sub>OH</sub>	Output High Voltage	I <sub>OH</sub> = -2mA	2.0	—	V

5639 tbl 08

### NOTE:

- At V<sub>DD</sub> ≤ 2.0V leakages are undefined.



## DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range ( $V_{DD} = 2.5V \pm 100mV$ )

Symbol	Parameter	Test Condition	Version	70T35/34L20 (70T25/24L20) Com'l Only		70T35/34L25 (70T25/24L25) Com'l & Ind		Unit
				Typ. <sup>(2)</sup>	Max.	Typ. <sup>(2)</sup>	Max.	
I <sub>DD</sub>	Dynamic Operating Current (Both Ports Active)	$\overline{CE} = V_{IL}$ , Outputs Disabled $SEM = V_{IH}$ $f = f_{MAX}^{(3)}$	COM'L L	80	140	70	130	mA
			IND L	—	—	100	160	
ISB1	Standby Current (Both Ports - TTL Level Inputs)	$\overline{CE}_R$ and $\overline{CE}_L = V_{IH}$ $SEM_R = SEM_L = V_{IH}$ $f = f_{MAX}^{(3)}$	COM'L L	12	20	7	17	mA
			IND L	—	—	12	25	
ISB2	Standby Current (One Port - TTL Level Inputs)	$\overline{CE}^*_A = V_{IL}$ and $\overline{CE}^*_B = V_{IH}^{(1)}$ Active Port Outputs Disabled, $f = f_{MAX}^{(3)}$ $SEM_R = SEM_L = V_{IH}$	COM'L L	55	90	40	80	mA
			IND L	—	—	55	100	
ISB3	Full Standby Current (Both Ports - CMOS Level Inputs)	Both Ports $\overline{CE}_L$ and $\overline{CE}_R \geq V_{DD} - 0.2V$ , $V_{IN} \geq V_{DD} - 0.2V$ or $V_{IN} < 0.2V$ , $f = 0^{(4)}$ $SEM_R = SEM_L \geq V_{DD} - 0.2V$	COM'L L	0.05	2.5	0.05	2.5	mA
			IND L	—	—	0.2	5.0	
ISB4	Full Standby Current (One Port - CMOS Level Inputs)	$\overline{CE}^*_A < 0.2V$ and $\overline{CE}^*_B \geq V_{DD} - 0.2V^{(1)}$ $SEM_R = SEM_L \geq V_{DD} - 0.2V$ $V_{IN} \geq V_{DD} - 0.2V$ or $V_{IN} < 0.2V$ Active Port Outputs Disabled, $f = f_{MAX}^{(3)}$	COM'L L	55	90	40	80	mA
			IND L	—	—	55	100	

**NOTES:**

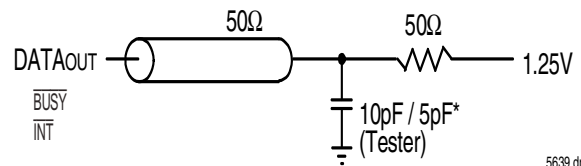
- Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- $V_{DD} = 2.5V$ ,  $T_A = +25^\circ C$ , and are not production tested. I<sub>DD</sub> dc = 85mA (typ.)
- At  $f = f_{MAX}$ , address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/trc, and using "AC Test Conditions" of input levels of GND to 3V.
- $f = 0$  means no address or control lines change.

5639 tbl 09

## AC Test Conditions

Input Pulse Levels	GND to 2.5V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.25V
Output Reference Levels	1.25V
Output Load	Figure 1

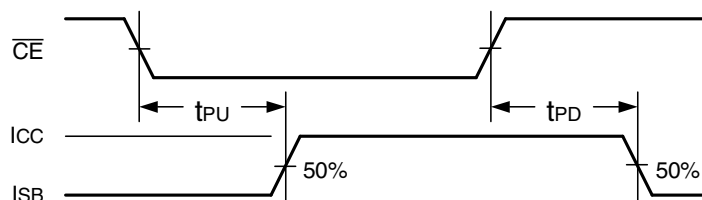
5639 tbl 10



5639 drw 06

Figure 1. AC Output Test Load  
\*(For tLZ, tHZ, tWZ, tOW)

## Timing of Power-Up Power-Down



5639 drw 07

## AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range

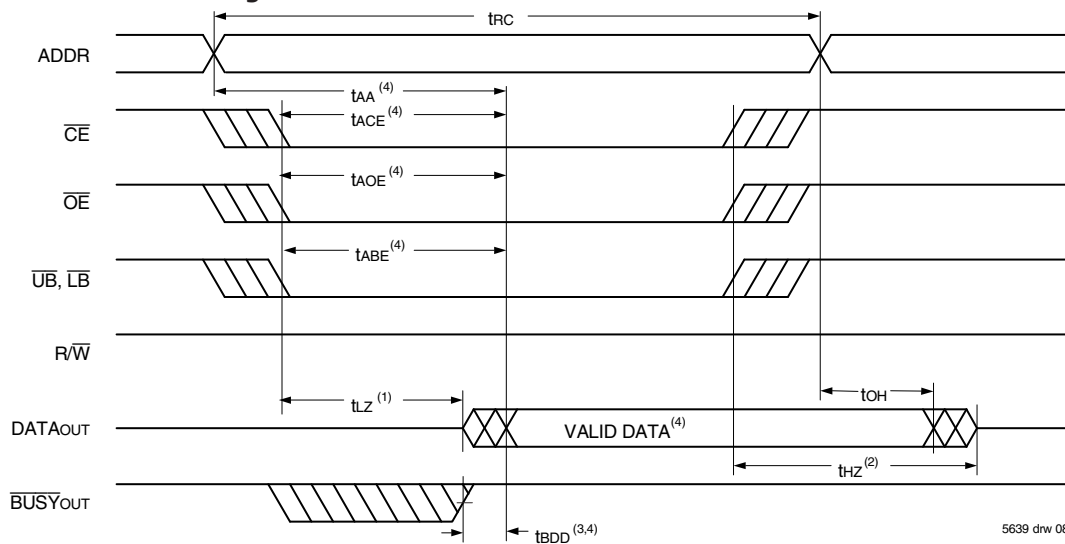
Symbol	Parameter	70T35/34L20 (70T25/24L20) Com'I Only		70T35/34L25 (70T25/24L25) Com'I & Ind		Unit
		Min.	Max.	Min.	Max.	
<b>READ CYCLE</b>						
t <sub>RC</sub>	Read Cycle Time	20	—	25	—	ns
t <sub>AA</sub>	Address Access Time	—	20	—	25	ns
t <sub>ACE</sub>	Chip Enable Access Time <sup>(3)</sup>	—	20	—	25	ns
t <sub>ABE</sub>	Byte Enable Access Time <sup>(3)</sup>	—	20	—	25	ns
t <sub>AOE</sub>	Output Enable Access Time <sup>(3)</sup>	—	12	—	13	ns
t <sub>OH</sub>	Output Hold from Address Change	3	—	3	—	ns
t <sub>LZ</sub>	Output Low-Z Time <sup>(1,2)</sup>	3	—	3	—	ns
t <sub>HZ</sub>	Output High-Z Time <sup>(1,2)</sup>	—	12	—	15	ns
t <sub>PU</sub>	Chip Enable to Power Up Time <sup>(1,2)</sup>	0	—	0	—	ns
t <sub>PD</sub>	Chip Disable to Power Down Time <sup>(1,2)</sup>	—	20	—	25	ns
t <sub>SOP</sub>	Semaphore Flag Update Pulse ( $\overline{OE}$ or $\overline{SEM}$ )	10	—	10	—	ns
t <sub>SAA</sub>	Semaphore Address Access <sup>(3)</sup>	—	20	—	25	ns

**NOTES:**

5639 tbl 11

1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 1).
2. This parameter is guaranteed by device characterization, but is not production tested.
3. To access RAM,  $\overline{CE} = V_{IL}$ ,  $\overline{UB}$  or  $\overline{LB} = V_{IL}$ , and  $\overline{SEM} = V_{IH}$ . To access semaphore,  $\overline{CE} = V_{IH}$  or  $\overline{UB} \& \overline{LB} = V_{IH}$ , and  $\overline{SEM} = V_{IL}$ .

### Waveform of Read Cycles<sup>(5)</sup>



**NOTES:**

1. Timing depends on which signal is asserted last,  $\overline{OE}$ ,  $\overline{CE}$ ,  $\overline{LB}$ , or  $\overline{UB}$ .
2. Timing depends on which signal is de-asserted first,  $\overline{CE}$ ,  $\overline{OE}$ ,  $\overline{LB}$ , or  $\overline{UB}$ .
3.  $t_{BDD}$  delay is required only in case where opposite port is completing a write operation to the same address location for simultaneous read operations  $\overline{BUSY}$  has no relation to valid output data.
4. Start of valid data depends on which timing becomes effective last  $t_{ABE}$ ,  $t_{AOE}$ ,  $t_{ACE}$ ,  $t_{AA}$  or  $t_{BDD}$ .
5.  $\overline{SEM} = V_{IH}$ .

## AC Electrical Characteristics Over the Operating Temperature and Supply Voltage

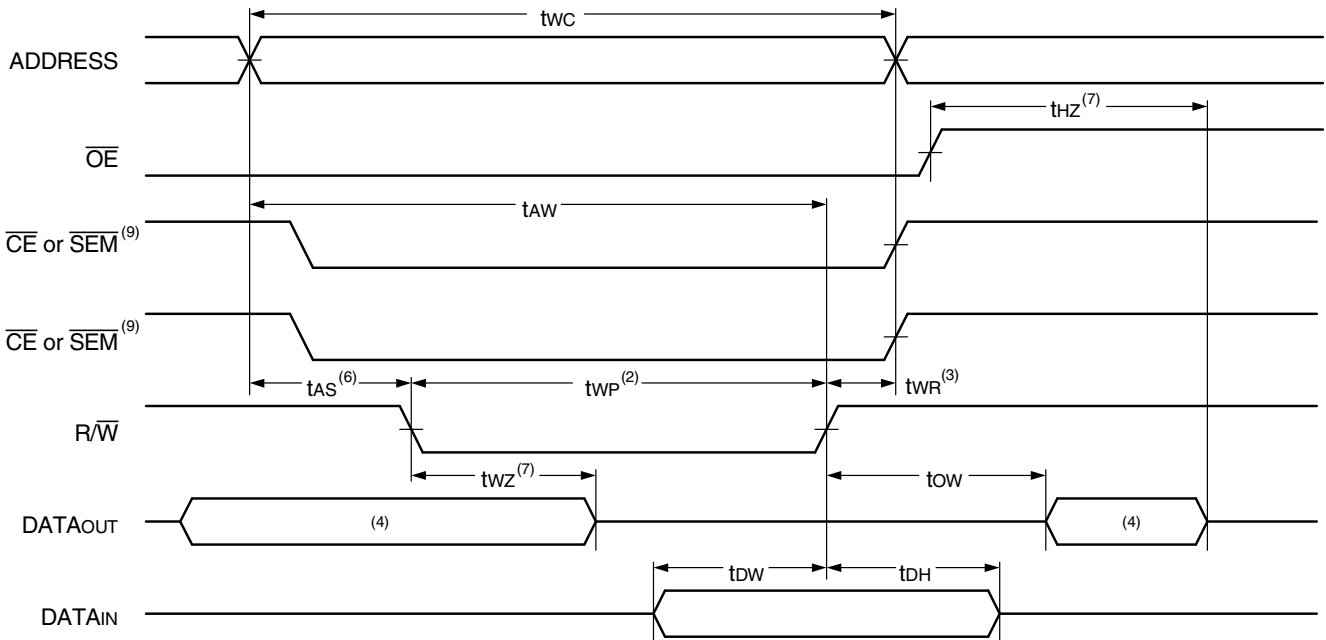
Symbol	Parameter	70T35/34L20 (70T25/24L20) Com'l Only		70T35/34L25 (70T25/24L25) Com'l & Ind		Unit
		Min.	Max.	Min.	Max.	
<b>WRITE CYCLE</b>						
t <sub>WC</sub>	Write Cycle Time	20	—	25	—	ns
t <sub>EW</sub>	Chip Enable to End-of-Write <sup>(3)</sup>	15	—	20	—	ns
t <sub>AW</sub>	Address Valid to End-of-Write	15	—	20	—	ns
t <sub>AS</sub>	Address Set-up Time <sup>(3)</sup>	0	—	0	—	ns
t <sub>WP</sub>	Write Pulse Width	15	—	20	—	ns
t <sub>WR</sub>	Write Recovery Time	0	—	0	—	ns
t <sub>DW</sub>	Data Valid to End-of-Write	15	—	15	—	ns
t <sub>HZ</sub>	Output High-Z Time <sup>(1,2)</sup>	—	12	—	15	ns
t <sub>DH</sub>	Data Hold Time <sup>(4)</sup>	0	—	0	—	ns
t <sub>WZ</sub>	Write Enable to Output in High-Z <sup>(1,2)</sup>	—	12	—	15	ns
t <sub>OW</sub>	Output Active from End-of-Write <sup>(1,2,4)</sup>	0	—	0	—	ns
t <sub>SWRD</sub>	$\overline{\text{SEM}}$ Flag Write to Read Time	5	—	5	—	ns
t <sub>SPS</sub>	$\overline{\text{SEM}}$ Flag Contention Window	5	—	5	—	ns

5639 tbl 12

### NOTES:

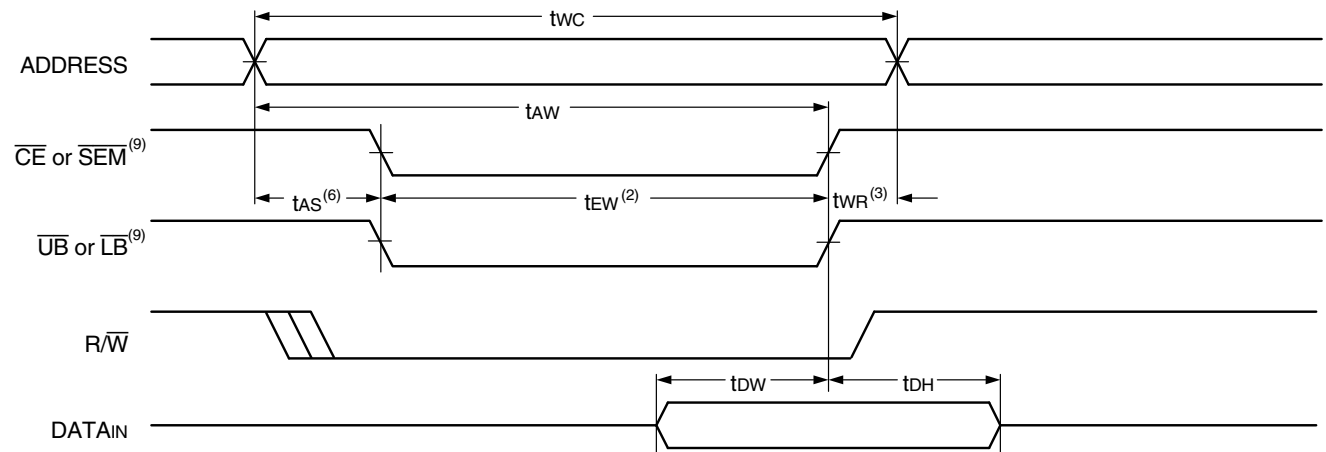
1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 1).
2. This parameter is guaranteed by device characterization, but is not production tested.
3. To access SRAM,  $\overline{\text{CE}} = V_{IL}$ ,  $\overline{\text{UB}}$  or  $\overline{\text{LB}} = V_{IL}$ ,  $\overline{\text{SEM}} = V_{IH}$ . To access semaphore,  $\overline{\text{CE}} = V_{IH}$  or  $\overline{\text{UB}} \& \overline{\text{LB}} = V_{IH}$ , and  $\overline{\text{SEM}} = V_{IL}$ . Either condition must be valid for the entire t<sub>EW</sub> time.
4. The specification for t<sub>DH</sub> must be met by the device supplying write data to the SRAM under all operating conditions. Although t<sub>DH</sub> and t<sub>OW</sub> values will vary over voltage and temperature, the actual t<sub>DH</sub> will always be smaller than the actual t<sub>OW</sub>.

### Timing Waveform of Write Cycle No. 1, R/W Controlled Timing<sup>(1,5,8)</sup>



5639 drw 09

### Timing Waveform of Write Cycle No. 2, CE, UB, LB Controlled Timing<sup>(1,5)</sup>

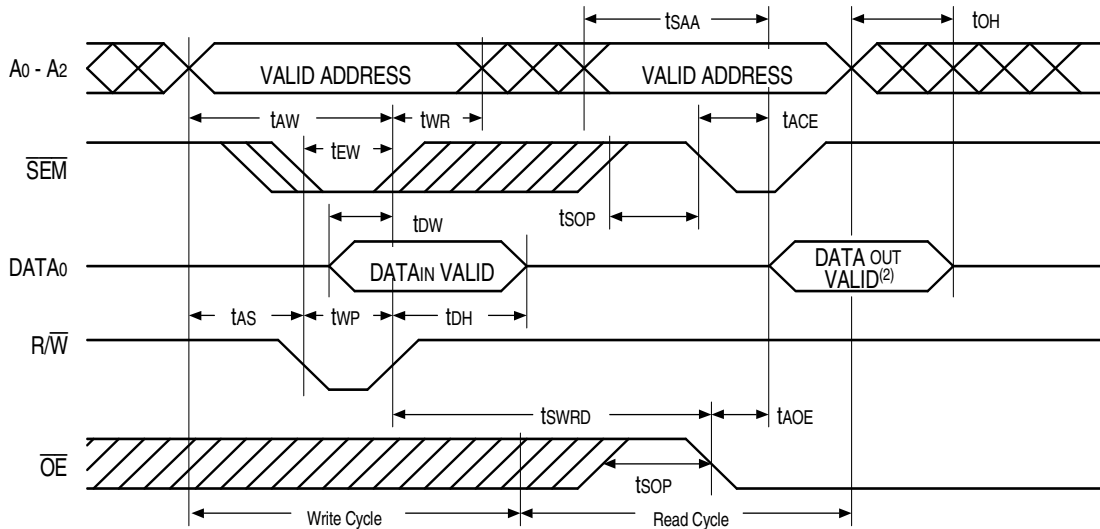


5639 drw 10

**NOTES:**

1. R/W or CE or UB & LB must be HIGH during all address transitions.
2. A write occurs during the overlap (tEW or tWP) of a LOW UB or LB and a LOW CE and a LOW R/W for memory array writing cycle.
3. tWR is measured from the earlier of CE or R/W (or SEM or R/W) going HIGH to the end-of-write cycle.
4. During this period, the I/O pins are in the output state and input signals must not be applied.
5. If the CE or SEM LOW transition occurs simultaneously with or after the R/W LOW transition the outputs remain in the HIGH-impedance state.
6. Timing depends on which enable signal is asserted last, CE, R/W, or UB or LB.
7. This parameter is guaranteed by device characterization, but is not production tested. Transition is measured 0mV from steady state with Output Test Load (Figure 1).
8. If OE is LOW during R/W controlled write cycle, the write pulse width must be the larger of tWP or (twz + tdw) to allow the I/O drivers to turn off and data to be placed on the bus for the required tOW. If OE is HIGH during an R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified tWP.
9. To access SRAM, CE = VIL, UB or LB = VIL, and SEM = VIH. To access Semaphore, CE = VIH or UB and LB = VIH, and SEM = VIL. tEW must be met for either condition.

### Timing Waveform of Semaphore Read after Write Timing, Either Side<sup>(1)</sup>

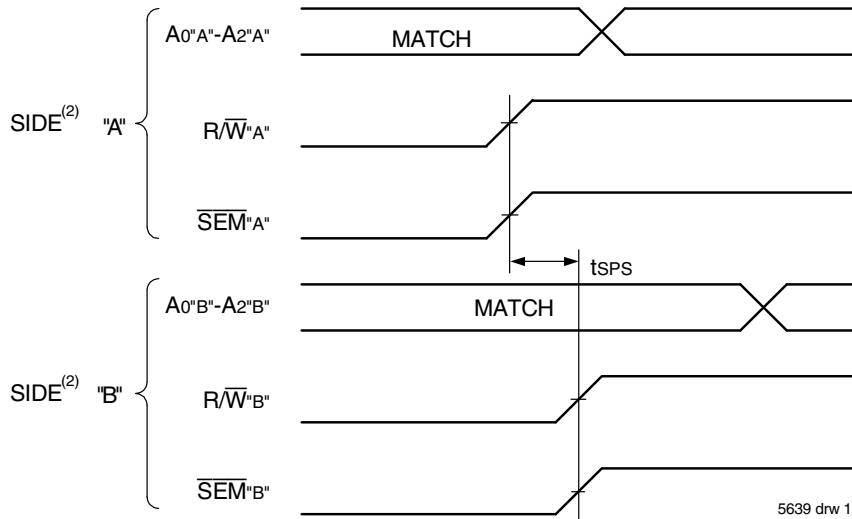


5639 drw 11

NOTES:

- $\overline{CE} = V_{IH}$  or  $\overline{UB} \& \overline{LB} = V_{IH}$  for the duration of the above timing (both write and read cycle).
- "DATAOUT VALID" represents all I/O's (I/O<sub>0</sub>-I/O<sub>17</sub> for IDT70T35/34) and (I/O<sub>0</sub>-I/O<sub>15</sub> for IDT70T25/24) equal to the semaphore value.

### Timing Waveform of Semaphore Write Contention<sup>(1,3,4)</sup>



5639 drw 12

NOTES:

- $D_{OR} = D_{OL} = V_{IL}$ ,  $\overline{CE}_R = \overline{CE}_L = V_{IH}$ , or both  $\overline{UB} \& \overline{LB} = V_{IH}$ .
- All timing is the same for left and right port. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- This parameter is measured from  $R/\overline{W}^A$  or  $\overline{SEM}^A$  going HIGH to  $R/\overline{W}^B$  or  $\overline{SEM}^B$  going HIGH.
- If  $t_{SPS}$  is not satisfied, there is no guarantee which side will obtain the semaphore flag.

## AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range

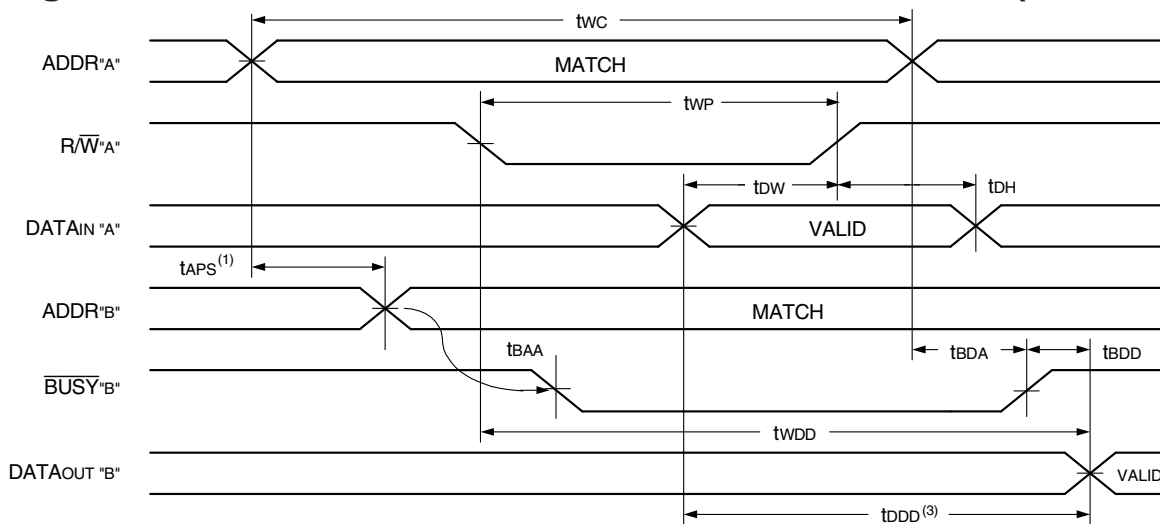
Symbol	Parameter	70T35/34L20 (70T25/24L20) Com'l Only		70T35/34L25 (70T25/24L25) Com'l & Ind		Unit
		Min.	Max.	Min.	Max.	
<b>BUS<math>\bar{Y}</math> TIMING (<math>M/\bar{S} = V_{IH}</math>)</b>						
t <sub>BAA</sub>	$\bar{B}US\bar{Y}$ Access Time from Address Match	—	20	—	20	ns
t <sub>BDA</sub>	$\bar{B}US\bar{Y}$ Disable Time from Address Not Matched	—	20	—	20	ns
t <sub>BAC</sub>	$\bar{B}US\bar{Y}$ Access Time from Chip Enable LOW	—	20	—	20	ns
t <sub>BDC</sub>	$\bar{B}US\bar{Y}$ Disable Time from Chip Enable HIGH	—	17	—	17	ns
t <sub>APS</sub>	Arbitration Priority Set-up Time <sup>(2)</sup>	5	—	5	—	ns
t <sub>BDD</sub>	$\bar{B}US\bar{Y}$ Disable to Valid Data <sup>(3)</sup>	—	30	—	30	ns
t <sub>WH</sub>	Write Hold After $\bar{B}US\bar{Y}$ <sup>(5)</sup>	15	—	17	—	ns
<b>BUS<math>\bar{Y}</math> TIMING (<math>M/\bar{S} = V_{IL}</math>)</b>						
t <sub>WB</sub>	$\bar{B}US\bar{Y}$ Input to Write <sup>(4)</sup>	0	—	0	—	ns
t <sub>WH</sub>	Write Hold After $\bar{B}US\bar{Y}$ <sup>(5)</sup>	15	—	17	—	ns
<b>PORT-TO-PORT DELAY TIMING</b>						
t <sub>WDD</sub>	Write Pulse to Data Delay <sup>(1)</sup>	—	45	—	50	ns
t <sub>D</sub> DD	Write Data Valid to Read Data Delay <sup>(1)</sup>	—	35	—	35	ns

5639 tbl 13

**NOTES:**

1. Port-to-port delay through SRAM cells from writing port to reading port, refer to "TIMING WAVEFORM OF WRITE PORT-TO-PORT READ AND  $\bar{B}US\bar{Y}$  ( $M/\bar{S} = V_{IH}$ )".
2. To ensure that the earlier of the two ports wins.
3. t<sub>BDD</sub> is a calculated parameter and is the greater of 0, t<sub>WDD</sub> – t<sub>WP</sub> (actual) or t<sub>DD</sub> – t<sub>DW</sub> (actual).
4. To ensure that the write cycle is inhibited during contention.
5. To ensure that a write cycle is completed after contention.

### Timing Waveform of Write Port-to-Port Read and $\bar{B}US\bar{Y}$ <sup>(2,4,5)</sup> ( $M/\bar{S} = V_{IH}$ )

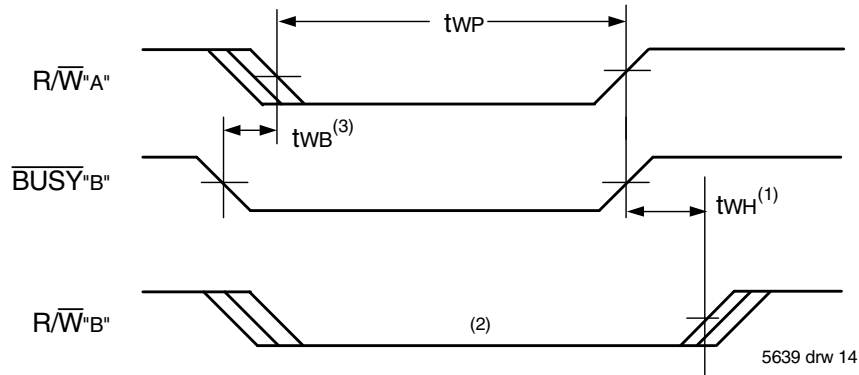


**NOTES:**

1. To ensure that the earlier of the two ports wins. t<sub>APs</sub> is ignored for  $M/\bar{S} = V_{IL}$  (slave).
2.  $\bar{C}E_L = \bar{C}E_R = V_{IL}$ .
3.  $\bar{O}E = V_{IL}$  for the reading port.
4. If  $M/\bar{S} = V_{IL}$  (slave),  $\bar{B}US\bar{Y}$  is an input. Then for this example  $\bar{B}US\bar{Y}$ 'A' =  $V_{IH}$  and  $\bar{B}US\bar{Y}$ 'B' input is shown above.
5. All timing is the same for both left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

5639 drw 13

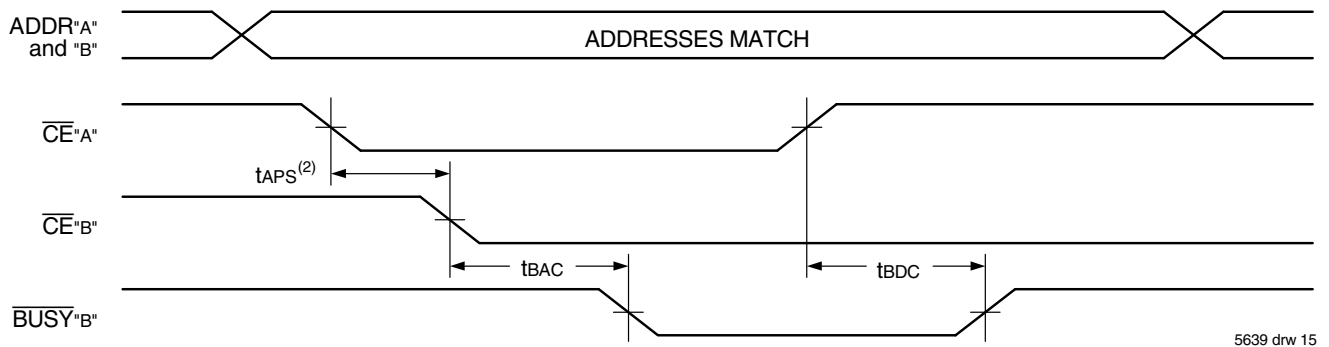
### Timing Waveform of Write with $\overline{\text{BUSY}}$



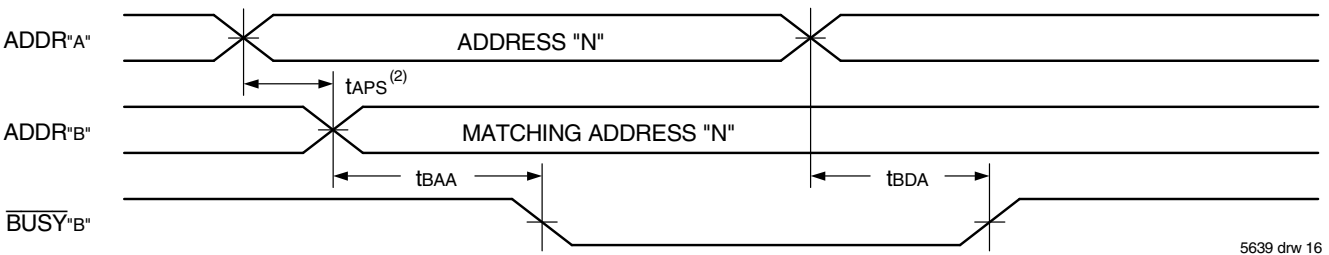
**NOTES:**

1.  $t_{WH}$  must be met for both master  $\overline{\text{BUSY}}$  input (slave) and output (master).
2.  $\overline{\text{BUSY}}$  is asserted on port "B" blocking  $R/\overline{W}$ "B", until  $\overline{\text{BUSY}}$ "B" goes HIGH.
3.  $t_{WB}$  is only for the slave version.

### Waveform of $\overline{\text{BUSY}}$ Arbitration Controlled by $\overline{\text{CE}}$ Timing<sup>(1)</sup> ( $M/\overline{S} = V_{IH}$ )



### Waveform of $\overline{\text{BUSY}}$ Arbitration Cycle Controlled by Address Match Timing<sup>(1)</sup> ( $M/\overline{S} = V_{IH}$ )



**NOTES:**

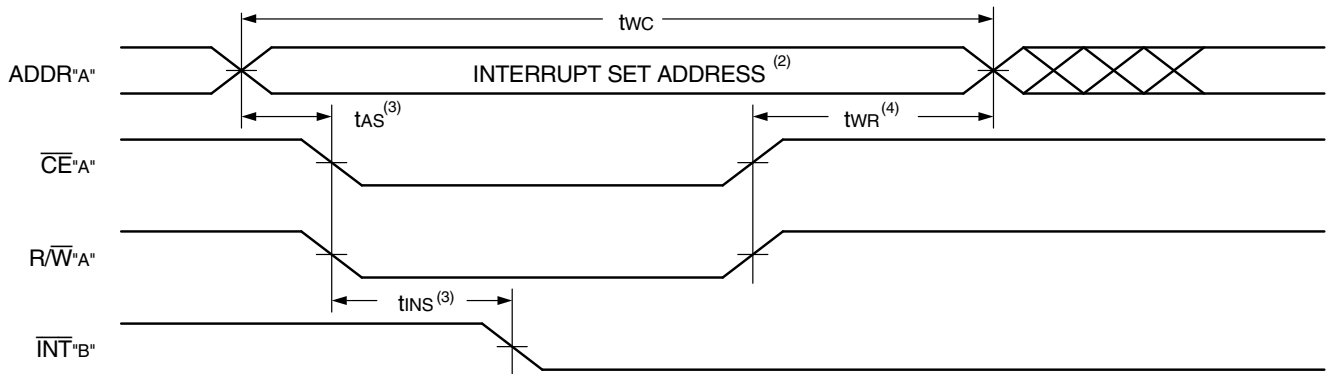
1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from "A".
2. If  $t_{APS}$  is not satisfied, the  $\overline{\text{BUSY}}$  signal will be asserted on one side or another but there is no guarantee on which side  $\overline{\text{BUSY}}$  will be asserted.

## AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range

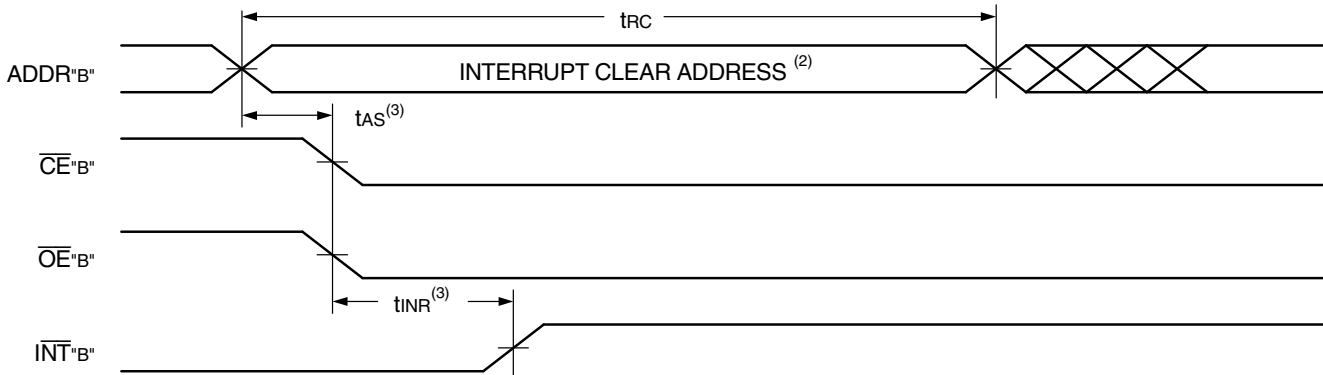
Symbol	Parameter	70T35/34L20 (70T25/24L20) Com'l Only		70T35/34L25 (70T25/24L25) Com'l & Ind		Unit
		Min.	Max.	Min.	Max.	
<b>INTERRUPT TIMING</b>						
t <sub>AS</sub>	Address Set-up Time	0	—	0	—	ns
t <sub>WR</sub>	Write Recovery Time	0	—	0	—	ns
t <sub>INS</sub>	Interrupt Set Time	—	20	—	20	ns
t <sub>INR</sub>	Interrupt Reset Time	—	20	—	20	ns

5639 tbl 14

### Waveform of Interrupt Timing<sup>(1)</sup>



5639 drw 17



5639 drw 18

#### NOTES:

1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from "A".
2. See Interrupt Flag Truth Table III.
3. Timing depends on which enable signal ( $\overline{CE}$  or  $R/\overline{W}$ ) is asserted last.
4. Timing depends on which enable signal ( $\overline{CE}$  or  $R/\overline{W}$ ) is de-asserted first.



### Truth Table III — Interrupt Flag<sup>(1)</sup>

Left Port					Right Port					Function
R/WL	CEL	OEL	A12L-A0L <sup>(4)</sup>	INTL	R/WR	CEr	OEr	A12R-A0R <sup>(4)</sup>	INTR	
L	L	X	1FFF	X	X	X	X	X	L <sup>(2)</sup>	Set Right INTR Flag
X	X	X	X	X	X	L	L	1FFF	H <sup>(3)</sup>	Reset Right INTR Flag
X	X	X	X	L <sup>(3)</sup>	L	L	X	1FFE	X	Set Left INTL Flag
X	L	L	1FFE	H <sup>(2)</sup>	X	X	X	X	X	Reset Left INTL Flag

**NOTES:**

- Assumes  $\overline{BUSY}_L = \overline{BUSY}_R = V_{IH}$ .
- If  $\overline{BUSY}_L = V_{IL}$ , then no change.
- If  $\overline{BUSY}_R = V_{IL}$ , then no change.
- A12 is a NC for IDT70T34 and IDT70T24, therefore Interrupt Addresses are FFF and FFE.

5639 tbl 15

### Truth Table IV — Address BUSY Arbitration

Inputs			Outputs		Function
CEL	CEr	A12L-A0L <sup>(4)</sup> A12R-A0R	$\overline{BUSY}_L$ <sup>(1)</sup>	$\overline{BUSY}_R$ <sup>(1)</sup>	
X	X	NO MATCH	H	H	Normal
H	X	MATCH	H	H	Normal
X	H	MATCH	H	H	Normal
L	L	MATCH	(2)	(2)	Write Inhibit <sup>(3)</sup>

5639 tbl 16

**NOTES:**

- Pins  $\overline{BUSY}_L$  and  $\overline{BUSY}_R$  are both outputs when the part is configured as a master. Both are inputs when configured as a slave.  $\overline{BUSY}$  outputs on the IDT70T35/34L (IDT70T25/24L) are push pull, not open drain outputs. On slaves the  $\overline{BUSY}$  input internally inhibits writes.
- L if the inputs to the opposite port were stable prior to the address and enable inputs of this port. H if the inputs to the opposite port became stable after the address and enable inputs of this port. If tAPS is not met, either  $\overline{BUSY}_L$  or  $\overline{BUSY}_R = LOW$  will result.  $\overline{BUSY}_L$  and  $\overline{BUSY}_R$  outputs cannot be LOW simultaneously.
- Writes to the left port are internally ignored when  $\overline{BUSY}_L$  outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when  $\overline{BUSY}_R$  outputs are driving LOW regardless of actual logic level on the pin.
- A12 is a NC for IDT70T34 and IDT70T24. Address comparison will be for A0 - A11.

### Truth Table V — Example of Semaphore Procurement Sequence<sup>(1,2,3)</sup>

Functions	D0 - D17 Left <sup>(2)</sup>	D0 - D17 Right <sup>(2)</sup>	Status
No Action	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Right Port Writes "0" to Semaphore	0	1	No change. Right side has no write access to semaphore
Left Port Writes "1" to Semaphore	1	0	Right port obtains semaphore token
Left Port Writes "0" to Semaphore	1	0	No change. Left port has no write access to semaphore
Right Port Writes "1" to Semaphore	0	1	Left port obtains semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free
Right Port Writes "0" to Semaphore	1	0	Right port has semaphore token
Right Port Writes "1" to Semaphore	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free

**NOTES:**

- This table denotes a sequence of events for only one of the eight semaphores on the IDT70T35/34L (IDT70T25/24L).
- There are eight semaphore flags written to via I/O0 and read from all I/O's (I/O0-I/O17 for IDT70T35/34) and (I/O0-I/O15 for IDT70T25/24). These eight semaphores are addressed by A0-A2.
- CE = V<sub>IH</sub>, SEM = V<sub>IL</sub> to access the semaphores. Refer to the Semaphore Read/Write Control Truth Tables.

5639 tbl 17

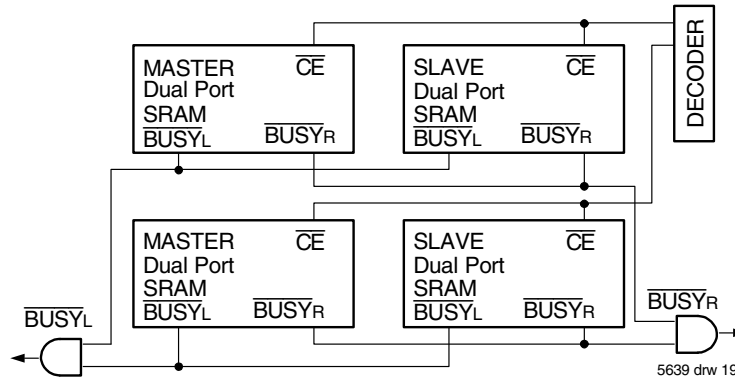


Figure 3. Busy and chip enable routing for both width and depth expansion with IDT70T35/34L (IDT70T25/24L) SRAMs.

## Functional Description

The IDT70T35/34L (IDT70T25/24L) provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT70T35/34L (IDT70T25/24L) has an automatic power down feature controlled by  $\overline{CE}$ . The  $\overline{CE}$  controls on-chip power down circuitry that permits the respective port to go into a standby mode when not selected ( $\overline{CE}$  HIGH). When a port is enabled, access to the entire memory array is permitted.

## Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag ( $\overline{INTL}$ ) is asserted when the right port writes to memory location 1FFE (HEX) (FFF for IDT70T34 and IDT70T24), where a write is defined as the  $\overline{CE}_R = R/\overline{W}_R = V_{IL}$  per Truth Table III. The left port clears the interrupt by an address location 1FFE access when  $\overline{CE}_L = \overline{OE}_L = V_{IL}$ ,  $R/\overline{W}_L$  is a "don't care". Likewise, the right port interrupt flag ( $\overline{INTR}$ ) is set when the left port writes to memory location 1FFF (HEX) (FFF for IDT70T34 and IDT70T24) and to clear the interrupt flag ( $\overline{INTR}$ ), the right port must read the memory location 1FFF. The message to the interrupt mail box is user-defined, since it is an addressable SRAM location. If the interrupt function is not used, the interrupt address locations are not used as mail boxes but as part of the random access memory.

## Busy Logic

Busy Logic provides a hardware indication that both ports of the SRAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the SRAM is "busy". The  $\overline{BUSY}$  pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a  $\overline{BUSY}$  indication, the write signal is gated internally to prevent the write from proceeding.

The use of  $\overline{BUSY}$  logic is not required or desirable for all applications. In some cases it may be useful to logically OR the  $\overline{BUSY}$  outputs together and use any  $\overline{BUSY}$  indication as an interrupt source to flag the event of an illegal or illogical operation. If the write inhibit function of  $\overline{BUSY}$  logic is not desirable, the  $\overline{BUSY}$  logic can be disabled by placing the part in slave mode with the  $M/\overline{S}$  pin. Once in slave mode the  $\overline{BUSY}$  pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the  $\overline{BUSY}$  pins HIGH. If desired, unintended write

operations can be prevented to a port by tying the  $\overline{BUSY}$  pin for that port LOW.

The  $\overline{BUSY}$  outputs on the IDT70T35/34L (IDT70T25/24L) SRAM in master mode, are push-pull type outputs and do not require pull up resistors to operate. If these SRAMs are being expanded in depth, then the  $\overline{BUSY}$  indication for the resulting array requires the use of an external AND gate.

## Width Expansion with Busy Logic Master/Slave Arrays

When expanding an IDT70T35/34L (IDT70T25/24L) SRAM array in width while using  $\overline{BUSY}$  logic, one master part is used to decide which side of the SRAM array will receive a  $\overline{BUSY}$  indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master, use the  $\overline{BUSY}$  signal as a write inhibit signal. Thus on the IDT70T35/34L (IDT70T25/24L) SRAM the  $\overline{BUSY}$  pin is an output if the part is used as a master ( $M/\overline{S}$  pin =  $V_{IH}$ ), and the  $\overline{BUSY}$  pin is an input if the part used as a slave ( $M/\overline{S}$  pin =  $V_{IL}$ ) as shown in Figure 3.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating  $\overline{BUSY}$  on one side of the array and another master indicating  $\overline{BUSY}$  on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The  $\overline{BUSY}$  arbitration, on a master, is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a  $\overline{BUSY}$  flag to be output from the master before the actual write pulse can be initiated with either the  $R/\overline{W}$  signal or the byte enables. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

## Semaphores

The IDT70T35/34L (IDT70T25/24L) is an extremely fast Dual-Port 8/4K x 18 (8/4K x 16) CMOS Static RAM with an additional 8 address locations dedicated to binary semaphore flags. These flags allow either processor on the left or right side of the Dual-Port SRAM to claim a privilege over the other processor for functions defined by the system designer's software. As an example, the semaphore can be used by one processor

to inhibit the other from accessing a portion of the Dual-Port SRAM or any other shared resource.

The Dual-Port SRAM features a fast access time, and both ports are completely independent of each other. This means that the activity on the left port in no way slows the access time of the right port. Both ports are identical in function to standard CMOS Static RAM and can be accessed at the same time with the only possible conflict arising from the simultaneous writing of, or a simultaneous READ/WRITE of, a non-semaphore location. Semaphores are protected against such ambiguous situations and may be used by the system program to avoid any conflicts in the non-semaphore portion of the Dual-Port SRAM. These devices have an automatic power-down feature controlled by CE, the Dual-Port SRAM enable, and SEM, the semaphore enable. The CE and SEM pins control on-chip power down circuitry that permits the respective port to go into standby mode when not selected. This is the condition which is shown in Truth Table I where CE and SEM are both HIGH.

Systems which can best use the IDT70T35/34L (IDT70T25/24L) contain multiple processors or controllers and are typically very high-speed systems which are software controlled or software intensive. These systems can benefit from a performance increase offered by the IDT70T35/34L (IDT70T25/24L)'s hardware semaphores, which provide a lockout mechanism without requiring complex programming.

Software handshaking between processors offers the maximum in system flexibility by permitting shared resources to be allocated in varying configurations. The IDT70T35/34L (IDT70T25/24L) does not use its semaphore flags to control any resources through hardware, thus allowing the system designer total flexibility in system architecture.

An advantage of using semaphores rather than the more common methods of hardware arbitration is that wait states are never incurred in either processor. This can prove to be a major advantage in very high-speed systems.

## How the Semaphore Flags Work

The semaphore logic is a set of eight latches which are independent of the Dual-Port SRAM. These latches can be used to pass a flag, or token, from one port to the other to indicate that a shared resource is in use. The semaphores provide a hardware assist for a use assignment method called "Token Passing Allocation." In this method, the state of a semaphore latch is used as a token indicating that shared resource is in use. If the left processor wants to use this resource, it requests the token by setting the latch. This processor then verifies its success in setting the latch by reading it. If it was successful, it proceeds to assume control over the shared resource. If it was not successful in setting the latch, it determines that the right side processor has set the latch first, has the token and is using the shared resource. The left processor can then either repeatedly request that semaphore's status or remove its request for that semaphore to perform another task and occasionally attempt again to gain control of the token via the set and test sequence. Once the right side has relinquished the token, the left side should succeed in gaining control.

The semaphore flags are active LOW. A token is requested by writing a zero into a semaphore latch and is released when the same side writes a one to that latch.

The eight semaphore flags reside within the IDT70T35/34L (IDT70T25/24L) in a separate memory space from the Dual-Port SRAM. This address space is accessed by placing a LOW input on

the  $\overline{\text{SEM}}$  pin (which acts as a chip select for the semaphore flags) and using the other control pins (Address,  $\overline{\text{OE}}$ , and  $\text{R}/\overline{\text{W}}$ ) as they would be used in accessing a standard static RAM. Each of the flags has a unique address which can be accessed by either side through address pins A0 – A2. When accessing the semaphores, none of the other address pins has any effect.

When writing to a semaphore, only data pin D0 is used. If a LOW level is written into an unused semaphore location, that flag will be set to a zero on that side and a one on the other side (see Truth Table V). That semaphore can now only be modified by the side showing the zero. When a one is written into the same location from the same side, the flag will be set to a one for both sides (unless a semaphore request from the other side is pending) and then can be written to by both sides. The fact that the side which is able to write a zero into a semaphore subsequently locks out writes from the other side is what makes semaphore flags useful in interprocessor communications. (A thorough discussion on the use of this feature follows shortly.) A zero written into the same location from the other side will be stored in the semaphore request latch for that side until the semaphore is freed by the first side.

When a semaphore flag is read, its value is spread into all data bits so that a flag that is a one reads as a one in all data bits and a flag containing a zero reads as all zeros. The read value is latched into one side's output register when that side's semaphore select ( $\overline{\text{SEM}}$ ) and output enable ( $\overline{\text{OE}}$ ) signals go active. This serves to disallow the semaphore from changing state in the middle of a read cycle due to a write cycle from the other side. Because of this latch, a repeated read of a semaphore in a test loop must cause either signal ( $\overline{\text{SEM}}$  or  $\overline{\text{OE}}$ ) to go inactive or the output will never change.

A sequence WRITE/READ must be used by the semaphore in order to guarantee that no system level contention will occur. A processor requests access to shared resources by attempting to write a zero into a semaphore location. If the semaphore is already in use, the semaphore request latch will contain a zero, yet the semaphore flag will appear as one, a fact which the processor will verify by the subsequent read (see Truth Table V). As an example, assume a processor writes a zero to the left port at a free semaphore location. On a subsequent read, the processor will verify that it has written successfully to that location and will assume control over the resource in question. Meanwhile, if a processor on the right side attempts to write a zero to the same semaphore flag it will fail, as will be verified by the fact that a one will be read from that semaphore on the right side during subsequent read. Had a sequence of READ/WRITE been used instead, system contention problems could have occurred during the gap between the read and write cycles.

It is important to note that a failed semaphore request must be followed by either repeated reads or by writing a one into the same location. The reason for this is easily understood by looking at the simple logic diagram of the semaphore flag in Figure 4. Two semaphore request latches feed into a semaphore flag. Whichever latch is first to present a zero to the semaphore flag will force its side of the semaphore flag LOW and the other side HIGH. This condition will continue until a one is written to the same semaphore request latch. Should the other side's semaphore request latch have been written to a zero in the meantime, the semaphore flag will flip over to the other side as soon as a one is written into the first side's request latch. The second side's flag will now stay LOW until its semaphore request latch is written to

a one. From this it is easy to understand that, if a semaphore is requested and the processor which requested it no longer needs the resource, the entire system can hang up until a one is written into that semaphore request latch.

The critical case of semaphore timing is when both sides request a single token by attempting to write a zero into it at the same time. The semaphore logic is specially designed to resolve this problem. If simultaneous requests are made, the logic guarantees that only one side receives the token. If one side is earlier than the other in making the request, the first side to make the request will receive the token. If both requests arrive at the same time, the assignment will be arbitrarily made to one port or the other.

One caution that should be noted when using semaphores is that semaphores alone do not guarantee that access to a resource is secure. As with any powerful programming technique, if semaphores are misused or misinterpreted, a software error can easily happen.

Initialization of the semaphores is not automatic and must be handled via the initialization program at power-up. Since any semaphore request flag which contains a zero must be reset to a one, all semaphores on both sides should have a one written into them at initialization from both sides to assure that they will be free when needed.

## Using Semaphores—Some Examples

Perhaps the simplest application of semaphores is their application as resource markers for the IDT70T35/34L (IDT70T25/24L)'s Dual-Port SRAM. Say for example, the 8K x 18 SRAM was to be divided into two 4K x 18 blocks which were to be dedicated at any one time to servicing either the left or right port. Semaphore 0 could be used to indicate the side which would control the lower section of memory, and Semaphore 1 could be defined as the indicator for the upper section of memory.

To take a resource, in this example the lower 4K of Dual-Port SRAM, the processor on the left port could write and then read a zero into Semaphore 0. If this task were successfully completed (a zero was read back rather than a one), the left processor would assume control of the lower 4K. Meanwhile the right processor was attempting to gain control of the resource after the left processor, it would read back a one in response to the zero it had attempted to write into Semaphore 0. At this point, the software could choose to try and gain control of the second

4K section by writing, then reading a zero into Semaphore 1. If it succeeded in gaining control, it would lock out the left side.

Once the left side was finished with its task, it would write a one to Semaphore 0 and may then try to gain access to Semaphore 1. If Semaphore 1 was still occupied by the right side, the left side could undo its semaphore request and perform other tasks until it was able to write, then read a zero into Semaphore 1. If the right processor performs a similar task with Semaphore 0, this protocol would allow the two processors to swap 4K blocks of Dual-Port SRAM with each other.

The blocks do not have to be any particular size and can even be variable, depending upon the complexity of the software using the semaphore flags. All eight semaphores could be used to divide the Dual-Port SRAM or other shared resources into eight parts. Semaphores can even be assigned different meanings on different sides rather than being given a common meaning as was shown in the example above.

Semaphores are a useful form of arbitration in systems like disk interfaces where the CPU must be locked out of a section of memory during a transfer and the I/O device cannot tolerate any wait states. With the use of semaphores, once the two devices has determined which memory area was "off-limits" to the CPU, both the CPU and the I/O devices could access their assigned portions of memory continuously without any wait states.

Semaphores are also useful in applications where no memory "WAIT" state is available on one or both sides. Once a semaphore handshake has been performed, both processors can access their assigned RAM segments at full speed.

Another application is in the area of complex data structures. In this case, block arbitration is very important. For this application one processor may be responsible for building and updating a data structure. The other processor then reads and interprets that data structure. If the interpreting processor reads an incomplete data structure, a major error condition may exist. Therefore, some sort of arbitration must be used between the two different processors. The building processor arbitrates for the block, locks it and then is able to go in and update the data structure. When the update is completed, the data structure block is released. This allows the interpreting processor to come back and read the complete data structure, thereby guaranteeing a consistent data structure.

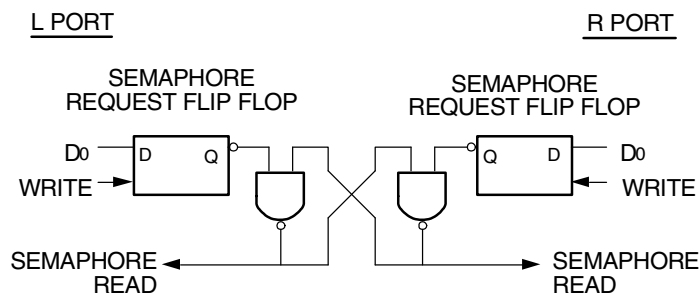
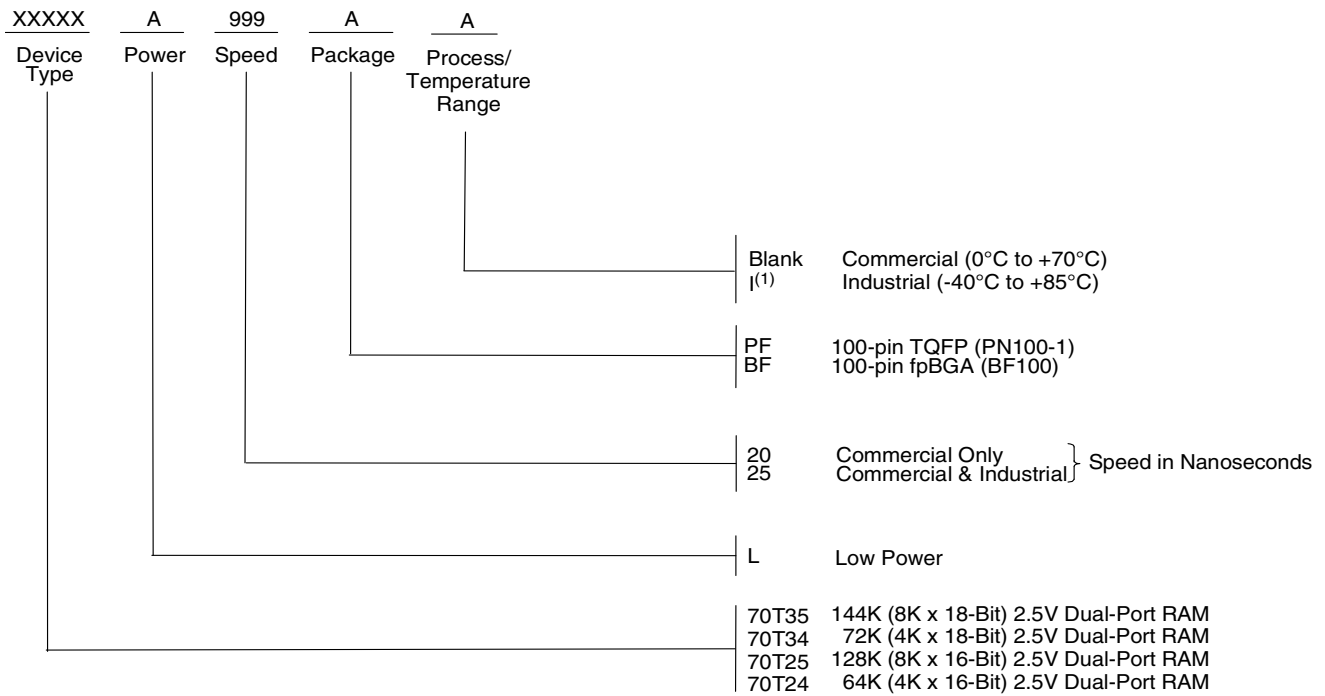


Figure 4. IDT70T35/34L (IDT70T25/24L) Semaphore Logic 5639 drw 20

## Ordering Information<sup>(1)</sup>



5639 drw 21

### NOTE:

- Contact your local sales office for Industrial temp range in other speeds, packages and powers.

## Preliminary Datasheet: Definition

"PRELIMINARY" datasheets contain descriptions for products that are in early release.

## Datasheet Document History

- 07/18/02: Initial Public Offering
- 12/06/02: Consolidated multiple devices into one data sheet
- 01/29/09: Page 21 Removed "IDT" from orderable part number
- 04/26/09: PDN-F-09-01 issued. See IDT.com for PDN specifics
- 02/10/14: 70T35\_34\_25\_24 Datasheet changed to Obsolete Status



## Notice

1. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation or any other use of the circuits, software, and information in the design of your product or system. Renesas Electronics disclaims any and all liability for any losses and damages incurred by you or third parties arising from the use of these circuits, software, or information.
2. Renesas Electronics hereby expressly disclaims any warranties against and liability for infringement or any other claims involving patents, copyrights, or other intellectual property rights of third parties, by or arising from the use of Renesas Electronics products or technical information described in this document, including but not limited to, the product data, drawings, charts, programs, algorithms, and application examples.
3. No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of Renesas Electronics or others.
4. You shall not alter, modify, copy, or reverse engineer any Renesas Electronics product, whether in whole or in part. Renesas Electronics disclaims any and all liability for any losses or damages incurred by you or third parties arising from such alteration, modification, copying or reverse engineering.
5. Renesas Electronics products are classified according to the following two quality grades: "Standard" and "High Quality". The intended applications for each Renesas Electronics product depends on the product's quality grade, as indicated below.
  - "Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; industrial robots; etc.
  - "High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control (traffic lights); large-scale communication equipment; key financial terminal systems; safety control equipment; etc.Unless expressly designated as a high reliability product or a product for harsh environments in a Renesas Electronics data sheet or other Renesas Electronics document, Renesas Electronics products are not intended or authorized for use in products or systems that may pose a direct threat to human life or bodily injury (artificial life support devices or systems; surgical implantations; etc.), or may cause serious property damage (space system; undersea repeaters; nuclear power control systems; aircraft control systems; key plant systems; military equipment; etc.). Renesas Electronics disclaims any and all liability for any damages or losses incurred by you or any third parties arising from the use of any Renesas Electronics product that is inconsistent with any Renesas Electronics data sheet, user's manual or other Renesas Electronics document.
6. When using Renesas Electronics products, refer to the latest product information (data sheets, user's manuals, application notes, "General Notes for Handling and Using Semiconductor Devices" in the reliability handbook, etc.), and ensure that usage conditions are within the ranges specified by Renesas Electronics with respect to maximum ratings, operating power supply voltage range, heat dissipation characteristics, installation, etc. Renesas Electronics disclaims any and all liability for any malfunctions, failure or accident arising out of the use of Renesas Electronics products outside of such specified ranges.
7. Although Renesas Electronics endeavors to improve the quality and reliability of Renesas Electronics products, semiconductor products have specific characteristics, such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Unless designated as a high reliability product or a product for harsh environments in a Renesas Electronics data sheet or other Renesas Electronics document, Renesas Electronics products are not subject to radiation resistance design. You are responsible for implementing safety measures to guard against the possibility of bodily injury, injury or damage caused by fire, and/or danger to the public in the event of a failure or malfunction of Renesas Electronics products, such as safety design for hardware and software, including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult and impractical, you are responsible for evaluating the safety of the final products or systems manufactured by you.
8. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. You are responsible for carefully and sufficiently investigating applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive, and using Renesas Electronics products in compliance with all these applicable laws and regulations. Renesas Electronics disclaims any and all liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
9. Renesas Electronics products and technologies shall not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations. You shall comply with any applicable export control laws and regulations promulgated and administered by the governments of any countries asserting jurisdiction over the parties or transactions.
10. It is the responsibility of the buyer or distributor of Renesas Electronics products, or any other party who distributes, disposes of, or otherwise sells or transfers the product to a third party, to notify such third party in advance of the contents and conditions set forth in this document.
11. This document shall not be reprinted, reproduced or duplicated in any form, in whole or in part, without prior written consent of Renesas Electronics.
12. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products.

(Note1) "Renesas Electronics" as used in this document means Renesas Electronics Corporation and also includes its directly or indirectly controlled subsidiaries.

(Note2) "Renesas Electronics product(s)" means any product developed or manufactured by or for Renesas Electronics.

(Rev.4.0-1 November 2017)

## Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu,  
Koto-ku, Tokyo 135-0061, Japan  
[www.renesas.com](http://www.renesas.com)

## Contact Information

For further information on a product, technology, the most up-to-date version of a document, or your nearest sales office, please visit:  
[www.IDT.com/go/support](http://www.IDT.com/go/support)

## Trademarks

Renesas and the Renesas logo are trademarks of Renesas Electronics Corporation. All trademarks and registered trademarks are the property of their respective owners.